

NCD30S10WCP5

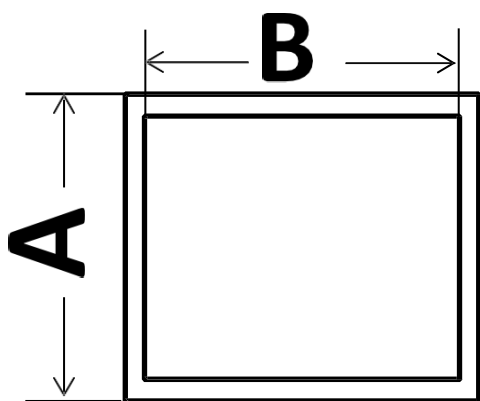
Planar MOS-Controlled Diode Wafer (PMCD)

Maximum Ratings @T_A=25°C (unless otherwise specified)

Parameter	Symbol	Ratings	Units
Working Peak Reverse Voltage	V _{RWM}	300	V
Average Rectified Forward	I _{F(AV)}	10	A
Non-repetitive Peak Surge Current (8.3ms,half sine wave) Rated load (JEDEC METHOD)	I _{FSM}	120	A
Operating Junction Temperature	T _J	175	°C

Electrical Characteristics @T_A=25°C

Parameter	Symbol	Test Condition	MIN.	TYP.	MAX.	Units
Breakdown Voltage	V _{BR}	I _R =0.05mA	300	-	-	V
Forward Voltage Drop	V _F	I _F =3A	-	-	0.84	V
		I _F =5A	-	-	0.87	V
		I _F =10A	-	-	0.98	V
Reverse Leakage Current	I _R	V _R =150V	-	-	10	μA



Item	Information
Die Size (A)	1909 μm
Top Metal Pad Size (B)	1702 μm
Passivation Seal	1839 μm
Wafer Thickness	260 μm
Gross Die Scribe Line Width	70 μm
Top Metal	Al
Back Metal	Ag
Gross Die	4380
Wafer Size	6"